L Number	Hits	Search Text	DB	Time stamp
1	1384	phase near3 chang\$3 near3 device	USPAT;	2003/10/31 06:39
!			US-PGPUB	i
2	564	(phase near3 chang\$3 near3 device) and (gate	USPAT;	2003/10/31 06:39
		electrode)	US-PGPUB	
3	174	((phase near3 chang\$3 near3 device) and	USPAT;	2003/10/31 06:24
ì		(gate electrode)) and etch\$3	US-PGPUB	.
4	732	phase near3 chang\$3 near3 device	EPO; JPO;	2003/10/31 06:39
			DERWENT;	į.
			IBM_TDB	i .
5	53	i	EPO; JPO;	2003/10/31 06:39
		electrode)	DERWENT;	\
Į.			IBM_TDB	
- ;	2202	tapered near5 electrode	USPAT;	2003/10/31 06:23
-			US-PGPUB	
	112	(tapered near5 electrode) and trench	USPAT;	2003/10/30 12:03
1			US-PGPUB	
	1182	tapered near5 electrode	EPO; JPO;	2003/10/30 12:02
			DERWENT;	
	_		IBM_TDB	1
- i	0	(tapered near5 electrode) and trench	USPAT;	2003/10/30 12:02
			US-PGPUB	1 /
-	0	(tapered near5 electrode) and (trench onen\$3	USPAT;	2003/10/30 12:03
j j	0000	recess hole via contact)	US-PGPUB	2000/10/20 15 05
-	2000	(tapered near5 electrode) and (trench onen\$3	USPAT;	2003/10/30 15:36
(1/15	recess hole via contact)	US-PGPUB	1 2002/10/20 15 15
-	1645	tapered near5 electrode	US-PGPUB;	2003/10/30 15:17
}			EPO; JPO;	
1		 	DERWENT;	
ļ	410	! (tapered near5 electrode) and (trench onen\$3	IBM_TDB	2002/10/20 15 22
	410	recess hole via contact)	EPO; JPO;	2003/10/30 15:32
		recess hore via contact;	DERWENT;	
_	77	((tapered near5 electrode) and (trench	IBM_TDB EPO; JPO;	2003/10/30 15:32
-	, ,	onen\$3 recess hole via contact)) and	DERWENT;	2003/10/30 15:32
		(semiconductor wafer)	IBM TDB	
_	2931	tapered near5 (electrode gate)	USPAT;	2003/10/30 15:36
1	2551	capeled hears (electrode gate)	US-PGPUB	2003/10/30 13.30
- 1	2649	(tapered near5 (electrode gate)) and (trench	USPAT;	2003/10/30 15:36
į.	015	onen\$3 recess hole via contact)	US-PGPUB	1 2003/10/30 13:30
- (1307	((tapered near5 (electrode gate)) and	USPAT;	2003/10/30 15:37
		(trench onen\$3 recess hole via contact)) and	US-PGPUB	2555, 25, 25 25151
		(semiconductor wafer substrate)	33 13132	
-	984		USPAT;	2003/10/30 15:37
		(trench onen\$3 recess hole via contact)) and	US-PGPUB	
		(semiconductor wafer substrate)) and etch\$3	I I	
- i	779	((((tapered near5 (electrode gate)) and	USPAT;	2003/10/30 15:45
ì		(trench onen\$3 recess hole via contact)) and	US-PGPUB	
}		(semiconductor wafer substrate)) and etch\$3)	}	İ
ļ		and mask	İ	
-	4471	phase near10 change near10 (device memory)	USPAT;	2003/10/30 15:45
ĺ			US-PGPUB	
- }	7	(phase near10 change near10 (device memory))	USPAT;	2003/10/30 15:46
l ì		and (tapered near5 (electrode gate))	US-PGPUB	
- !	4825	(gate electrode) near10 (etch\$3 pattern\$3)	USPAT;	2003/10/30 18:56
1		near100 mask near100 (trench hole open\$3 via	US-PGPUB	
1		contact recess groove)	1	<u> </u>
- <u> </u>	1481	((gate electrode) near10 (etch\$3 pattern\$3)	USPAT;	2003/10/30 18:56
	i	near100 mask near100 (trench hole open\$3 via	US-PGPUB	
-		contact recess groove)) and charge		
-	1471	(((gate electrode) near10 (etch\$3 pattern\$3)	USPAT;	2003/10/30 18:17
ļ		near100 mask near100 (trench hole open\$3 via	US-PGPUB	<u> </u>
Į		contact recess groove)) and charge) and	!	
ĺ		(semiconductor wafer substrate)	l	1
- 1	2095	(gate electrode) near10 (etch\$3 pattern\$3)	EPO; JPO;	2003/10/30 18:56
1		near100 mask near100 (trench hole open\$3 via	DERWENT;	İ
į		contact recess groove)	IBM_TDB	
-	45 j	((gate electrode) near10 (etch\$3 pattern\$3)	EPO; JPO;	2003/10/30 18:57
	ļ	near100 mask near100 (trench hole open\$3 via	DERWENT;	i
		contact recess groove)) and charge	IBM TDB	1